



DMT3003LFGQ

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C
30V	3.2mΩ @ V _{GS} = 10V	100A
	5.5mΩ @ V _{GS} = 4.5V	85A

Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Backlighting
- Power Management Functions
- DC-DC Converters

30V N-CHANNEL ENHANCEMENT MODE MOSFET

Features and Benefits

- Low R_{DS(ON)} Ensures On-State Losses are Minimized
- Excellent Q_{GD} × R_{DS(ON)} Product (FOM)
- Advanced Technology for DC-DC Converters
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Occupies Just 33% of the Board Area Occupied by SO-8 Enabling Smaller End Product
- 100% Unclamped Inductive Switching, Test in Production Ensures More Reliable And Robust End Application
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

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- Case: PowerDI[®]3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminal Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)

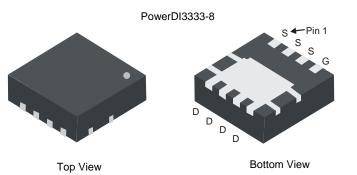
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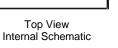
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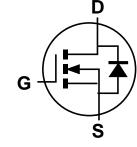
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Weight: 0.008 grams (Approximate)







Equivalent Circuit

Ordering Information (Note 5)

	Part Number	Case	Packaging		
	DMT3003LFGQ-7	PowerDI3333-8	2,000/Tape & Reel		
	DMT3003LFGQ-13	PowerDI3333-8	3,000/Tape & Reel		
Notes:	1, EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant, All applicable RoHS exemptions applied.				

EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/.

5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



SG2 = Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 18 = 2018) WW = Week Code (01 to 53)

PowerDI is a registered trademark of Diodes Incorporated. DMT3003LFGQ Document number: DS40819 Rev. 1 - 2



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V _{DSS}	30	V	
Gate-Source Voltage	V _{GSS}	±20	V	
Continuous Drain Current (Note 7) V _{GS} = 10V	T _C = +25°C T _C = +70°C	ID	100 90	А
Continuous Drain Current (Note 6) V _{GS} = 10V	ID	22 18	А	
Maximum Continuous Body Diode Forward Current (Note 6	Is	3	А	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	IDM	100	А	
Avalanche Current, L=1mH	I _{AS}	16	А	
Avalanche Energy, L=1mH	EAS	250	mJ	

Thermal Characteristics

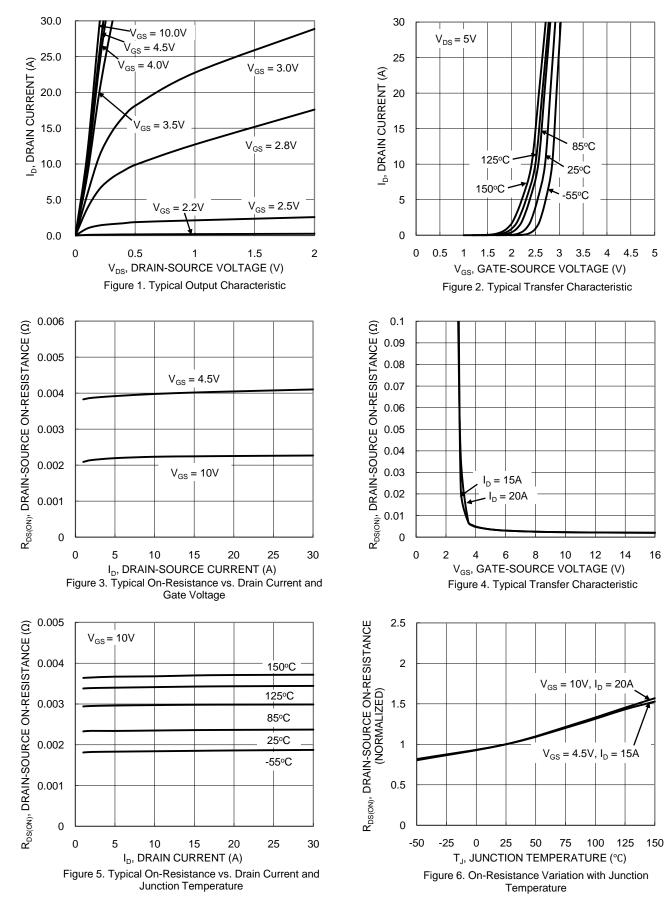
Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 6)	T _A = +25°C	PD	2.4	W
Thermal Resistance, Junction to Ambient (Note 6)		R _{θJA}	52	°C/W
Total Power Dissipation (Note 7)	T _C = +25°C	PD	62	W
Thermal Resistance, Junction to Case (Note 7)		R _{θJC}	2	°C/W
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

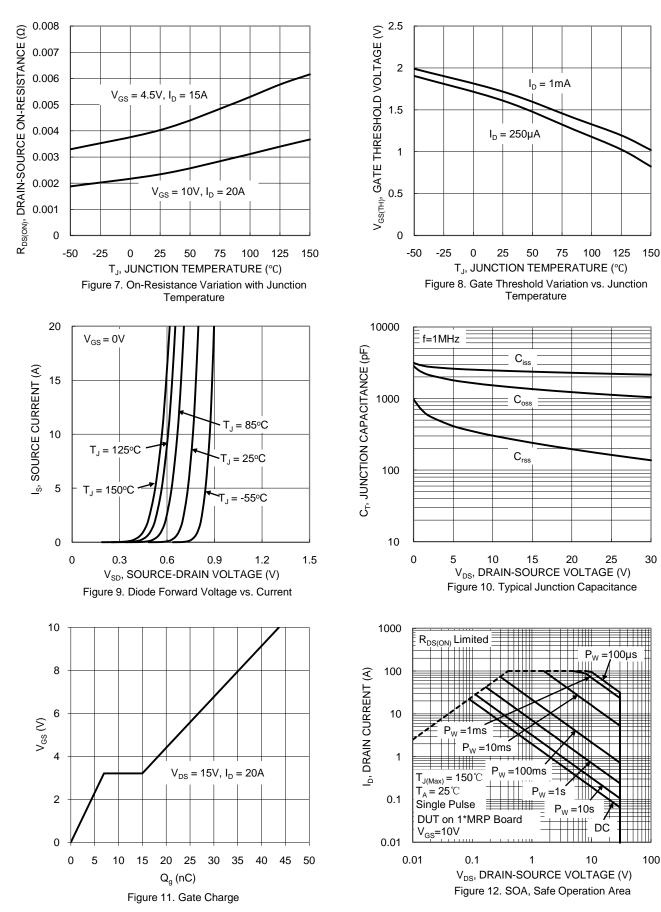
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV _{DSS}	30	—		V	$V_{GS} = 0V$, $I_D = 1mA$	
Zero Gate Voltage Drain Current	I _{DSS}		—	1	μA	$V_{DS} = 24V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}		_	±100	nA	V _{GS} = +20V, V _{DS} = 0V V _{GS} = -16V, V _{DS} = 0V	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V _{GS(TH)}	1	—	3	V	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	
Static Drain-Source On-Resistance		—	2.4	3.2		$V_{GS} = 10V, I_D = 20A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	—	4	5.5	mΩ	V _{GS} = 4.5V, I _D = 15A	
Diode Forward Voltage	V _{SD}	_	0.75	1	V	$V_{GS} = 0V, I_{S} = 10A$	
DYNAMIC CHARACTERISTICS (Note 9)						*	
Input Capacitance	CISS		2,370	—		V _{DS} = 15V, V _{GS} = 0V, f = 1MHz	
Output Capacitance	C _{OSS}	—	1,360	—	pF		
Reverse Transfer Capacitance	C _{RSS}	_	240	_			
Gate Resistance	R _G	—	0.6	—	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Q _G		20				
Total Gate Charge (V _{GS} = 10V)	Q _G	_	44	_	nC		
Gate-Source Charge	Q _{GS}	—	7	—	nc	$V_{DS} = 15V, I_D = 20A$	
Gate-Drain Charge	Q _{GD}	—	8	_			
Turn-On Delay Time	t _{D(ON)}	—	6.2	—		V _{DD} = 15V, V _{GS} = 10V, R _L = 0.75Ω, R _G = 3Ω, I _D = 20A	
Turn-On Rise Time	t _R	_	4.3	_			
Turn-Off Delay Time	t _{D(OFF)}		21	_	ns		
Turn-Off Fall Time	t _F		8	—			
Body Diode Reverse Recovery Time	t _{RR}		25	—	ns		
Body Diode Reverse Recovery Charge	Q _{RR}	—	37	—	nC	$I_F = 15A, di/dt = 500A/\mu s$	

 Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.
Thermal resistance from junction to soldering point (on the exposed drain pad).
Short duration pulse test used to minimize self-heating effect.
Guaranteed by design. Not subject to product testing. Notes:



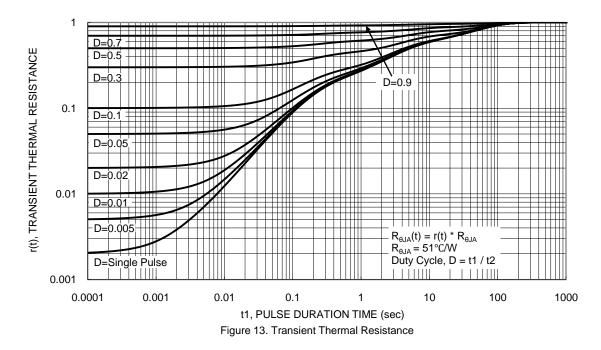






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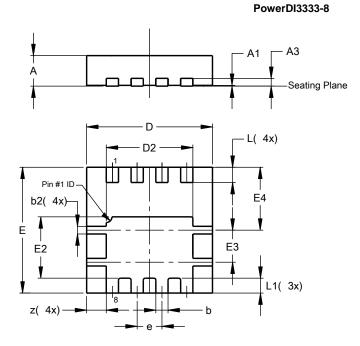






Package Outline Dimensions

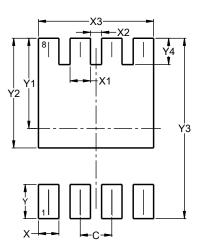
Please see http://www.diodes.com/package-outlines.html for the latest version.



PowerDI3333-8						
Dim	Min	Max	Тур			
Α	0.75	0.85	0.80			
A1	0.00	0.05	0.02			
A3	-	-	0.203			
b	0.27	0.37	0.32			
b2	0.15	0.25	0.20			
D	3.25	3.35	3.30			
D2	2.22	2.32	2.27			
Е	3.25	3.35	3.30			
E2	1.56	1.66	1.61			
E3	0.79	0.89	0.84			
E4	1.60	1.70	1.65			
е	_	-	0.65			
L	0.35	0.45	0.40			
L1	-	-	0.39			
z	-	-	0.515			
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions Value (in mm) 0.650 С Х 0.420 X1 0.420 X2 0.230 Х3 2.370 Υ 0.700 Y1 1.850 2.250 Y2 Y3 3.700 Y4 0.540

PowerDI3333-8



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